

**Low Capacitance Quad Array for ESD Protection**

**General Description**

This integrated transient voltage suppressor device (TVS) is designed for applications requiring transient overvoltage protection, printers, business machines, communication systems, medical equipment, and other applications. Its integrated design provides very effective and reliable protection for separate lines using only one package. These devices are ideal for situations where board space is at a premium.

**Applications**

- Serial and Parallel Ports
- Microprocessor Based Equipment
- Notebooks, Desktops, Servers
- Cellular and Portable Equipment

**Features**

- Four Separate Unidirectional Configurations for Protection
- Low Leakage Current < 1  $\mu$  A @ 3Volts
- Power Dissipation: 380mW
- Small SOT-563 SMT Package
- Low Capacitance
- Complies to USB 1.1 Low Speed & Speed Specifications
- These are Pb-Free Devices
- **Pb-Free package is available**  
RoHS product for packing code suffix "G"  
Halogen free product for packing code suffix "H"

**Complies with the following standards**

**IEC61000-4-2**

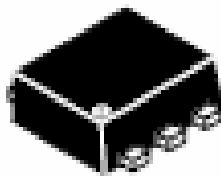
**Level 4 15 kV (air discharge)**

**8 kV(contact discharge)**

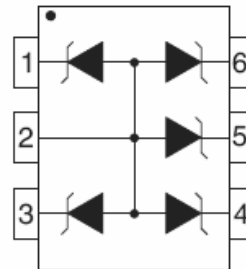
**MIL STD 883E - Method 3015-7 Class 3**

**25 kV HBM (Human Body Model)**

**Functional diagram**



**SOT-563**



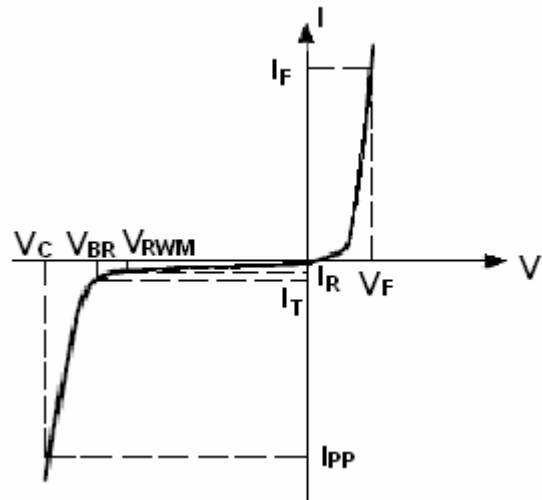
<b>Maximum Ratings (T<sub>A</sub>=25°C)</b>			
<b>Symbol</b>	<b>Parameter</b>	<b>Value</b>	<b>Units</b>
P <sub>PK</sub>	Peak Power Dissipation(8 × 20 $\mu$ s@T <sub>A</sub> =25°C)	25	W
P <sub>D</sub>	Steady State Power-1 Diode	380	mW
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient Above 25°C, Derate	327 3.05	°C/W Mw/°C
T <sub>Jmax</sub>	Maximum Junction Temperature	150	°C
T <sub>J</sub> T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55 to +150	°C
T <sub>L</sub>	Lead Solder Temperature(10 seconds duration)	260	°C



### Low Capacitance Quad Array for ESD Protection

#### Electrical Parameter

Symbol	Parameter
$I_{PP}$	Maximum Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Working Peak Reverse Voltage
$I_R$	Maximum Reverse Leakage Current @ $V_{RWM}$
$I_T$	Test Current
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_F$	Forward Current
$V_F$	Forward Voltage @ $I_F$



#### Electrical Characteristics

Part Numbers	$V_{BR}$			$I_T$	$V_{RWM}$	$I_R$	<b>C</b>
	Min.	Typ.	Max.				Typ. 0v bias
	V	V	V				pF
MSEMF3V3LCC	5.3	5.6	5.9	1	3.0	1.0	12

1. Non-repetitive current per Figure 1.
2. Only 1 diode under power. For 4 diodes under power
3. Capacitance of one diode at  $f=1\text{MHz}$ ,  $T_A=25^\circ\text{C}$

#### Typical Characteristics

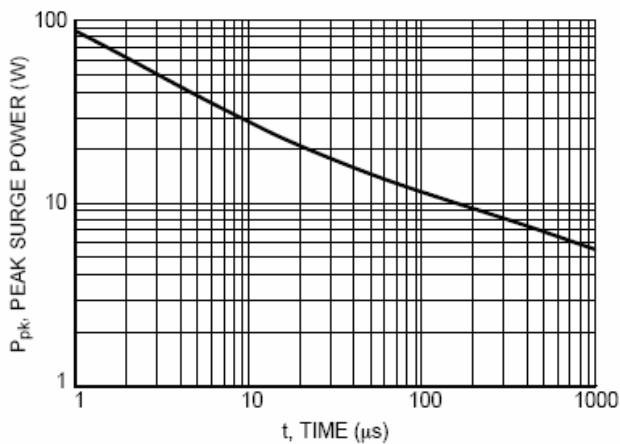


Figure 1 Pulse Width

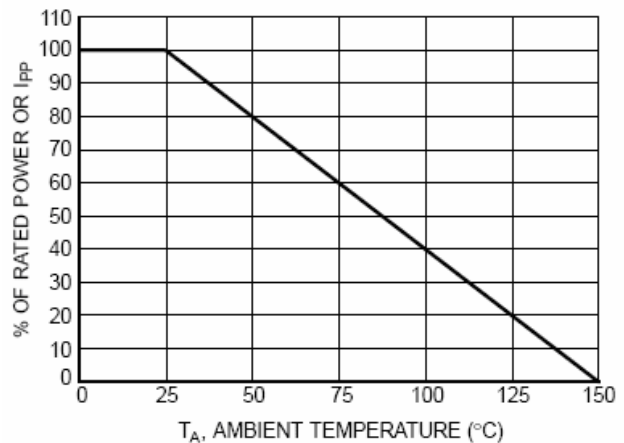
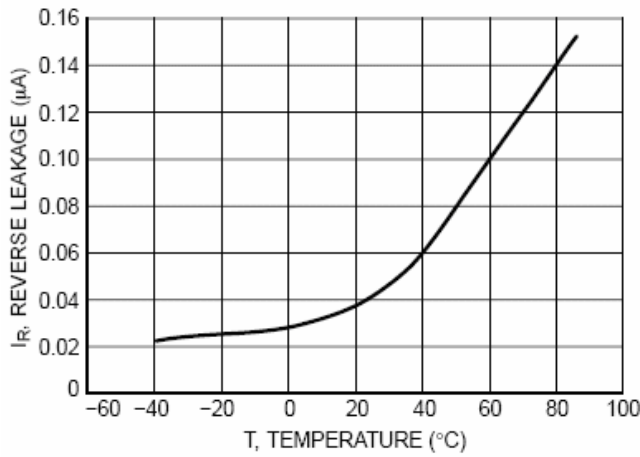
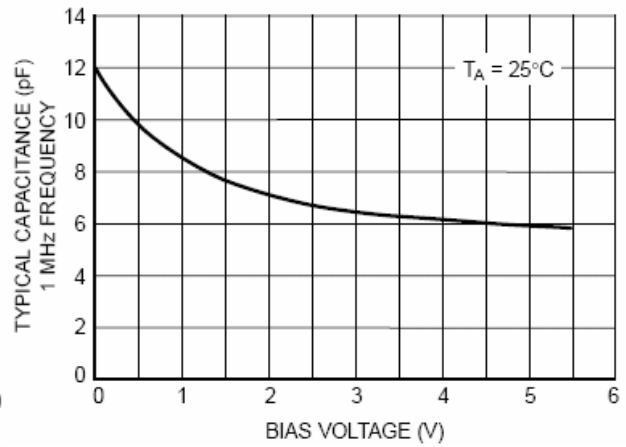


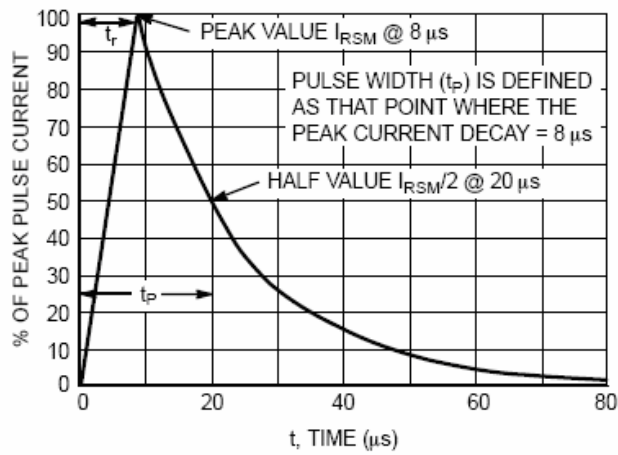
Figure 2 Power Derating Curve



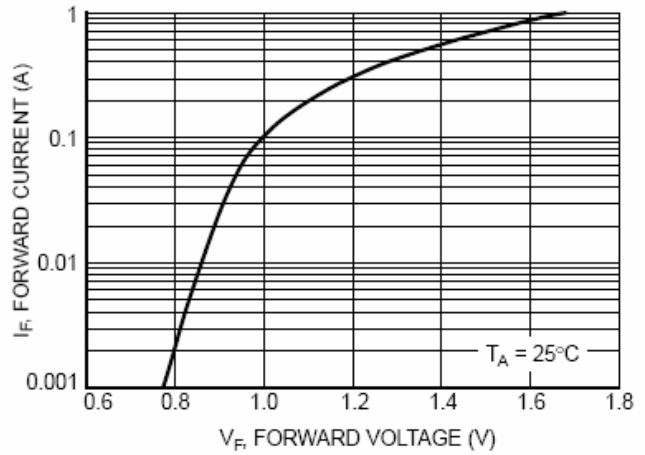
**Figure 3 Reverse Leakage versus temperature**



**Figure 4 Capacitance**



**Figure 5 8\*20 Pulse Waveform**

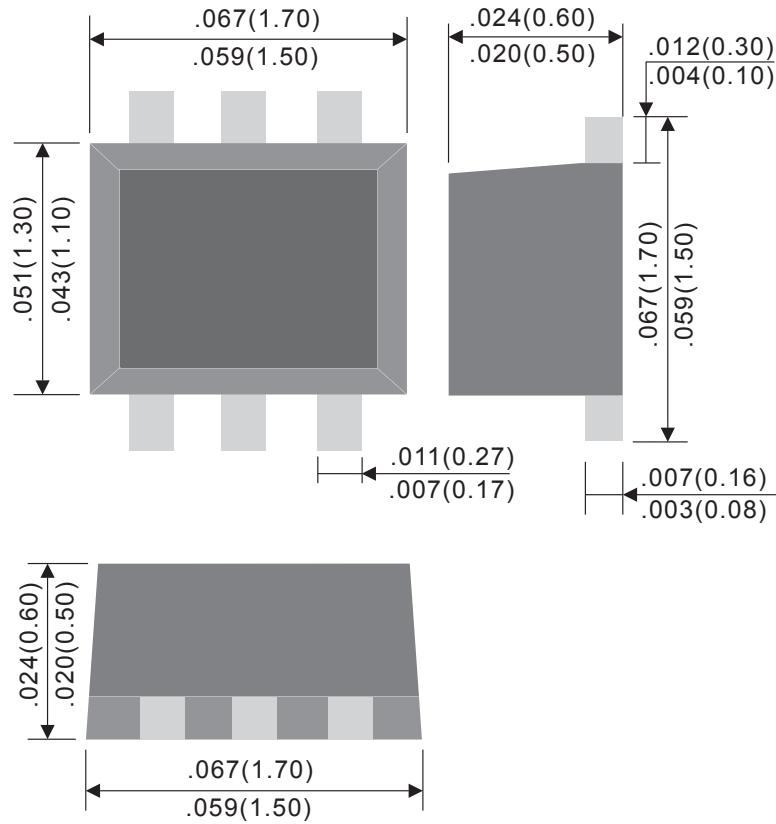


**Figure 6 Forward Voltage**



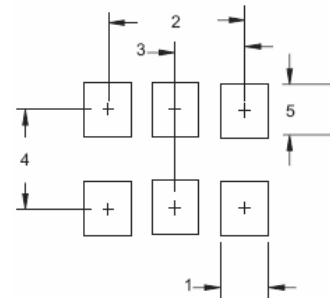
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### SOT-563 Mechanical Data



Dimensions in inches and (millimeters)

Typical		
DIM	MILLIMETERS	INCHES
1	0.30	0.012
2	1.02	0.040
3	0.51	0.020
4	1.40	0.055
5	0.51	0.020



Type number	Marking code
MSEMF3V3LCC	3C